50RIA Series

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Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 50 A



PRODUCT SUMMARY				
Package	TO-208AC (TO-65)			
Diode variation	Single SCR			
I _{T(AV)}	50 A			
V _{DRM} /V _{RRM}	100 V to 1200 V			
V _{TM}	1.60 V			
I _{GT}	100 mA			
TJ	- 40 °C to 125 °C			

FEATURES

- High current rating
- Excellent dynamic characteristics
- $dV/dt = 1000 V/\mu s$ option
- Superior surge capabilities
- Standard package
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- · Phase control applications in converters
- Lighting circuits
- Battery charges
- Regulated power supplies and temperature and speed control circuit
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

MAJOR RATINO	MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I		50	A						
I _{T(AV)}	T _C	94	°C						
I _{T(RMS)}		80	A						
less.	50 Hz	1430	٨						
I _{TSM}	60 Hz	1490	A						
l ² t	50 Hz	10.18	kA ² s						
1-1	60 Hz	9.30	KA-5						
V _{DRM} /V _{RRM}		100 to 1200	V						
t _q	Typical	110	μs						
TJ		- 40 to 125	°C						

ELECTRICAL SPECIFICATIONS

VOLTAGE	RATINGS	6		
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$
	10	100	150	
	20	200	300	
	40	400	500	
50RIA	60	600	700	15
	80	800	900	
	100	1000	1100	
	120	1200	1300	

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs ⁽²⁾ For voltage pulses with $t_p \le 5$ ms

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ABSOLUTE MAXIMUM RATII	NGS					
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current		180° cipucoi	180° sinusoidal conduction		50	А
at case temperature	I _{T(AV)}				94	°C
Maximum RMS on-state current	I _{T(RMS)}				80	А
		t = 10 ms	No voltage		1430	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		1490	А
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{BBM}		1200	A
	t = 8.3 ms	reapplied	Sinusoidal half wave,	1255		
Maximum I ² t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	10.18	kA ² s
	l ² t	t = 8.3 ms	reapplied		9.30	
	1-1	t = 10 ms	100 % V _{BBM}		7.20	
		t = 8.3 ms	reapplied		6.56	
Maximum I ² \sqrt{t} for fusing	l²√t		t = 0.1 to 10 ms, no voltage reapplied, T ₁ = T ₁ maximum			kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x I_{T}$	_(AV)), T _J = T _J maximum	0.94	v
High level value of threshold voltage	V _{T(TO)2}	(π x I _{T(AV)} < I	$<$ 20 x π x I _{T(AV)}),	T _J = T _J maximum	1.08	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}), \ T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r _{t2}	$(\pi \ge I_{T(AV)} < I < 20 \ge \pi \ge I_{T(AV)}), T_J = T_J maximum$			3.34	11122
Maximum on-state voltage	V _{TM}	I _{pk} = 157 A, T _J = 25 °C			1.60	V
Maximum holding current	I _H	T_J = 25 °C, anode supply 22 V, resistive load, initial I _T = 2 A			200	mA
Latching current	١L	Anode supp	ly 6 V, resistive lo	ad	400	

SWITCHING						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum rate of	$V_{DRM} \leq 600 \ V$	dl/dt	T _C = 125 °C, V _{DM} = Rated V _{DRM} , Gate pulse = 20 V, 15 Ω, t _p = 6 µs, t _r = 0.1 µs maximum	200	A/µs	
rise of turned-on current	$V_{DRM} \leq 1600 \ V$	di/di	$I_{TM} = (2 \text{ x rated dl/dt}) \text{ A}$	100		
Typical delay time		t _d	T_C = 25 °C, V_{DM} = Rated V_{DRM} , I_{TM} = 10 A dc resistive circuit Gate pulse = 10 V, 15 Ω source, t_p = 20 μs	0.9		
Typical turn-off time		tq	T_C = 125 °C, I_{TM} = 50 A, reapplied dV/dt = 20 V/µs dIr/dt = - 10 A/µs, V_R = 50 V	110	μs	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	200	V/us
off-state voltage	uv/ut	$T_J = T_J$ maximum linear to 67 % rated V_{DRM}	500 ⁽¹⁾	v/µs

Note

 $^{(1)}$ Available with dV/dt = 1000 V/µs, to complete code add S90 i.e. 50RIA120S90

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TRIGGERING					
PARAMETER	SYMBOL	TES	TEST CONDITIONS		UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum, $t_p \le t$	5 ms	10	W
Maximum average gate power	P _{G(AV)}			2.5	vv
Maximum peak positive gate current	I _{GM}			2.5	А
Maximum peak positive gate voltage	+V _{GM}			20	V
Maximum peak negative gate voltage	-V _{GM}			10	v
		T _J = - 40 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V	250	mA
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	
		T _J = 125 °C		50	
	N	T _J = - 40 °C	anode to cathode applied	3.5	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5	V
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated voltage	Maximum gate current/voltage not to trigger is the maximum	5.0	mA
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C		
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.35	K/W		
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased		r\/ VV		
		Non-lubricated threads	3.4 ^{+ 0 - 10} % (30)	N ⋅ m		
Allowable mounting torque		Lubricated threads	2.3 ^{+ 0 - 10} % (20)	(lbf · in)		
Approvimate weight			28	g		
Approximate weight			1.0	oz.		
Case style		See dimensions - link at the end of datasheet	TO-208A0	C (TO-65)		

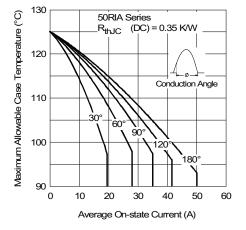
	N			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.078	0.057		
120°	0.094	0.098		
90°	0.120	0.130	$T_J = T_J maximum$	K/W
60°	0.176	0.183		
30°	0.294	0.296		

Note

The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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Fig. 1 - Current Ratings Characteristics

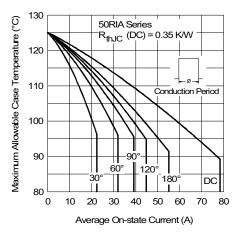


Fig. 2 - Current Ratings Characteristics

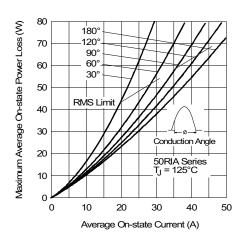


Fig. 3 - On-State Power Loss Characteristics

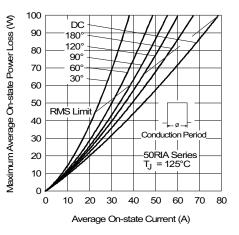


Fig. 4 - On-State Power Loss Characteristics

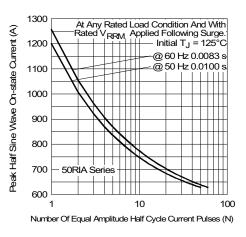


Fig. 5 - Maximum Non-Repetitive Surge Current

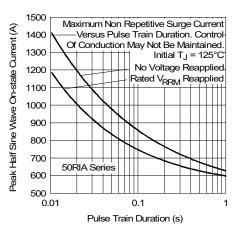


Fig. 6 - Maximum Non-Repetitive Surge Current

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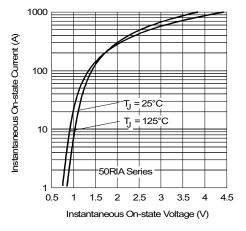


Fig. 7 - Forward Voltage Drop Characteristics

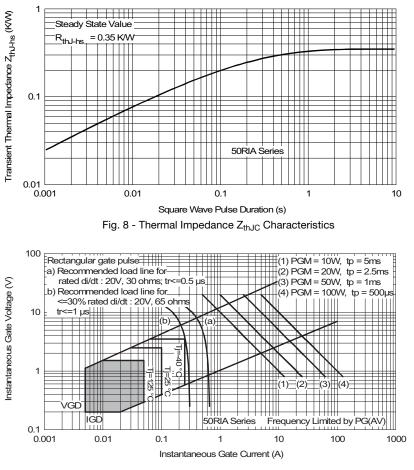


Fig. 9 - Gate Characteristics



ORDERING INFORMATION TABLE

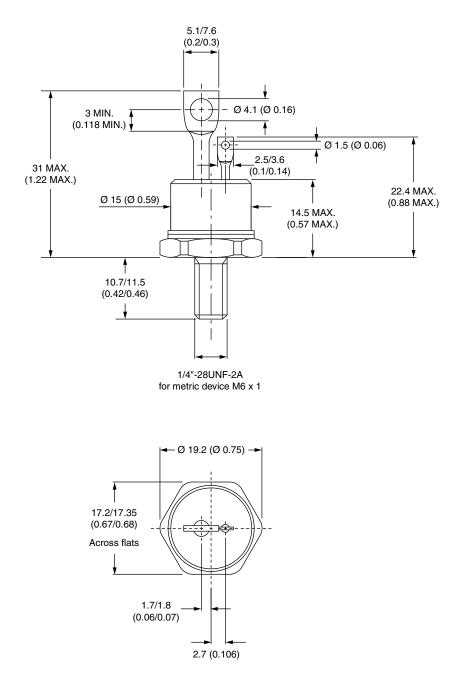
Device code	50	RIA	120	S90	М	l	
		2	3	4	5		
	1 -	Ess		art numb			
	3 - 4 -	Crit	ical dV/o	dt:		(see Voltag	e Ratings
	_	• S	90 = 100	00 V/µs	(specia	rd value) selection)	
	5 -					8AC (TO-6 C (TO-65) N	,

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95334			

VISHAY.

TO-208AC (TO-65)

DIMENSIONS in millimeters (inches)





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